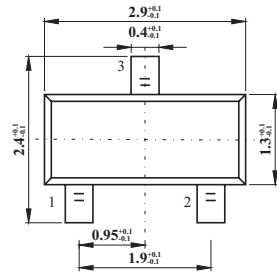
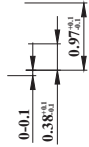


SOT-23

Unit: mm



$0.1^{+0.05}_{-0.015}$ 9 37:78mm05.201173 0 371173 0 0



- 1.Base
- 2.Emitter
- 3.collector



7D XQOHVV RWKHUZZLVH VSHFLILH

Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 μ A, V _{GS} =0V	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V			1	μ A
		V _{DS} =24V, V _{GS} =0V, T _J =55℃			5	
Gate-Body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =250 μ A	0.6	1	1.4	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =4A		45	55	mΩ
		V _{GS} =10V, I _D =4A T _J =125℃		66	80	
		V _{GS} =4.5V, I _D =3A		55	70	mΩ
		V _{GS} =2.5V, I _D =2A		83	110	mΩ
On state drain current	I _{D(ON)}	V _{GS} =4.5V, V _{DS} =5V	10			A
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =4A		8		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =15V, f=1MHz		390		pF
Output Capacitance	C _{oss}			54.5		pF
Reverse Transfer Capacitance	C _{rss}			41		pF
Gate resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz		3		Ω
Total Gate Charge	Q _g	V _{GS} =4.5V, V _{DS} =15V, I _D =-4A		4.34		nC
Gate Source Charge	Q _{gs}			0.6		nC
Gate Drain Charge	Q _{gd}			1.38		nC
Turn-On DelayTime	t _{D(on)}	V _{GS} =10V, V _{DS} =15V, R _L =3.75Ω, R _{GEN} =6Ω		3.3		ns
Turn-On Rise Time	t _r			1		ns
Turn-Off DelayTime	t _{D(off)}			21.7		ns
Turn-Off Fall Time	t _f			2.1		ns
Body Diode Reverse Recovery Time	t _{rr}	I _F =4A, di/dt=100A/μ s		12		ns
Body Diode Reverse Recovery Charge	Q _{rr}	I _F =4A, di/dt=100A/μ s		6.3		nC
Maximum Body-Diode Continuous Current	I _S				2.5	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V		0.8	1	V